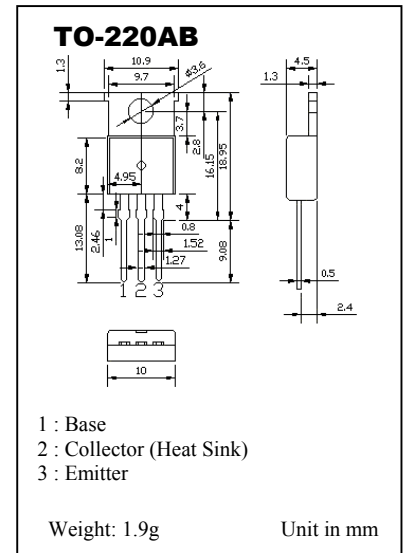


NPN SILICON EPITAXIAL TRANSISTOR

... designed for high voltage switching using in horizontal deflection output stage.

MAXIMUM RATINGS (T_c= 25 °C)

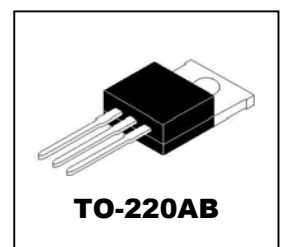
Characteristic	Symbol	Value	Unit
Collector Base Voltage	V _{CBO}	400	V
Collector Emitter Voltage	V _{CEO}	200	V
Emitter Base Voltage	V _{EBO}	6	V
Collector Current (DC)	I _c	7	A
Collector Current (Pulse)	I _{CP}	10	A
Base Current	I _B	4	A
Collector Power Dissipation	P _c	60	W
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _{stg}	-55 ~ 150	°C



ELECTRICAL CHARACTERISTICS (T_c= 25 °C)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Collector Cutoff Current	I _{CES}	V _{CE} =400V, V _{BE} =0	-	-	5	mA
		V _{CE} =250V, V _{BE} =0	-	-	100	μA
		V _{CE} =250V, V _{BE} =0, T _c =150°C	-	-	1	mA
Emitter Cutoff Current	I _{EBO}	V _{BE} =6V, I _c =0	-	-	1	mA
Collector Emitter Saturation Voltage	V _{CE(sat)}	I _B =0.5A, I _c =5A	-	-	1	V
Base Emitter Saturation Voltage	V _{BE(sat)}	I _B =0.5A, I _c =5A	-	-	1.2	V
Transition Frequency	f _T	V _{CE} =10V, I _c =0.5A	10	-	-	MHz
Turn Off Time	t _{off}	I _B =0.5A, I _c =5A	-	-	0.75	μs

**NPN SILICON
EPITAXIAL
TRANSISTOR**



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